

COMPUTER DIODE

200mA

Low Power, Switching

1N3600; JAN, JANTX & JANTXV 1N3600
1N4150; JAN, JANTX & JANTXV 1N4150
JAN, JANTX & JANTXV 1N4150-1

FEATURES

- Metallurgical Bond
- Qualified to MIL-S-19500/231
- Planar Passivated Chip
- DO-7 or DO-35 Package
- Non-JAN Available

DESCRIPTION

This series of switching diodes is useful in many computer switching applications, for both military and commercial systems.

5

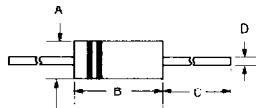
ABSOLUTE MAXIMUM RATINGS, AT 25°C

Reverse Breakdown Voltage	75V
Peak Working Voltage	50V
Average Output Current	200mA
Surge Current (1sec)	0.5A
(1 μ sec)	4.0A
Operating Temperature Range	-65°C to +175°C
Storage Temperature Range (1N4150)	-65°C to +200°C
(1N3600)	-65°C to +175°C

MECHANICAL SPECIFICATIONS

J, JTX & JTXV 1N3600

J, JTX & JTXV 1N4150, 1N4150-1



	INCHES	MILLIMETERS
A	.078-.107	1.98-2.72
B	.195-.300	4.96-7.62
C	1.0 MIN.-1.5 MAX.	25.4 MIN.-38.1 MAX.
D	.018-.022	.46-.56

	INCHES	MILLIMETERS
A	.066-.076	1.62-1.91
B	.140-.180	3.56-4.57
C	1.0 MIN.-1.5 MAX.	25.4 MIN.-38.1 MAX.
D	.018-.022	.46-.56

DO-7
1N3600

DO-35
1N4150



ELECTRICAL SPECIFICATIONS (at 25°C unless noted)

Characteristics	Forward Voltage	Forward Voltage	Forward Voltage	Forward Voltage	Forward Voltage	Reverse Breakdown Voltage
Conditions	V_{F1} $I_F = 1 \text{ mA DC}$	V_{F2} $I_F = 10 \text{ mA DC}$	V_{F3} $I_F = 50 \text{ mA DC (pulse)}$	V_{F4} $I_F = 100 \text{ mA DC (pulse)}$	V_{F5} $I_F = 200 \text{ mA DC (pulse)}$	BV $I_R = 5.0 \mu\text{A DC}$
Minimum Maximum	0.540 Vdc 0.620 Vdc	0.660 Vdc 0.740 Vdc	0.760 Vdc 0.860 Vdc	0.820 Vdc 0.920 Vdc	0.8/0 Vdc 1.00 Vdc	75 Vdc —

Characteristics	Reverse Current	Reverse Current	Junction Capacitance	Reverse Recovery Time	Reverse Recovery Time	Forward Recovery Time
Conditions	$I_R = 50 \text{ VDC}$	$I_R = 50 \text{ VDC}$ $T_A = 150^\circ\text{C}$	C $V_R = 0$ $F = 1 \text{ MHz}$ $V_{sig} = 50 \text{ mv (p-p)}$	$t_{rr1} = I_R = 10 \text{ to } 200 \text{ nsec}$ $R_L = 100 \text{ ohms}$	$t_{rr2} = I_F = I_R = 200 \text{ to } 400 \text{ nsec}$ $R_L = 100 \text{ ohms}$	$t_{fr} = I_F = 200 \text{ mA DC}$ $t_p = 100 \text{ nsec}$ $t_r = 0.4 \text{ nsec}$
Maximum	0.1 $\mu\text{A DC}$	100 $\mu\text{A DC}$	2.5 pf	4 nsec	6 nsec	10 nsec

